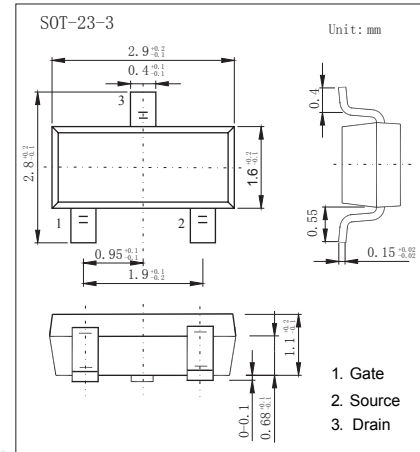
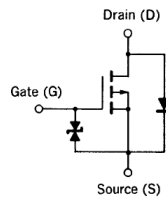


## P-Channel MOSFET

### 2SJ211

#### ■ Features

- $V_{DS} (V) = -100V$
- $I_D = -0.2 A$
- $R_{DS(ON)} < 20 \Omega$  ( $V_{GS} = -10V$ )
- $R_{DS(ON)} < 30 \Omega$  ( $V_{GS} = -4V$ )



#### ■ Absolute Maximum Ratings $T_a = 25^\circ C$

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	-100	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	
Continuous Drain Current	$I_D$	-0.2	A
Pulsed Drain Current (Note.1)	$I_{DM}$	-0.4	
Power Dissipation	$P_D$	0.2	W
Junction Temperature	$T_J$	150	$^\circ C$
Junction Storage Temperature Range	$T_{stg}$	-55 to 150	

Note.1:  $PW \leq 10$  ms, duty cycle  $\leq 50\%$

#### ■ Electrical Characteristics $T_a = 25^\circ C$

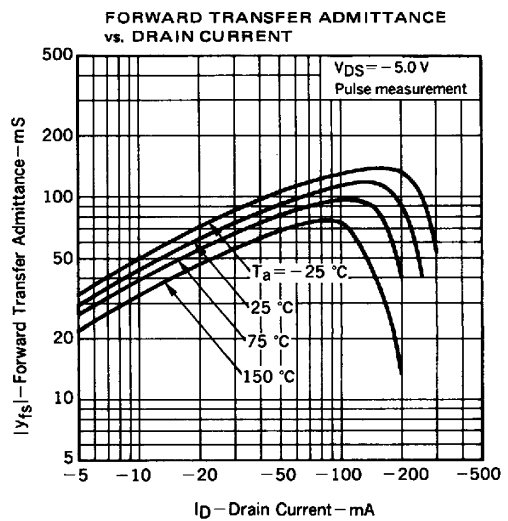
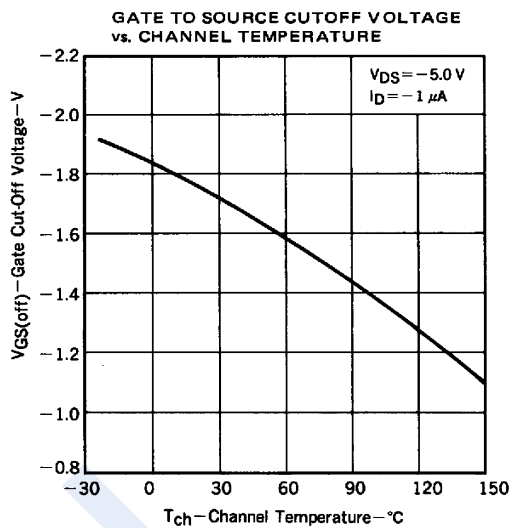
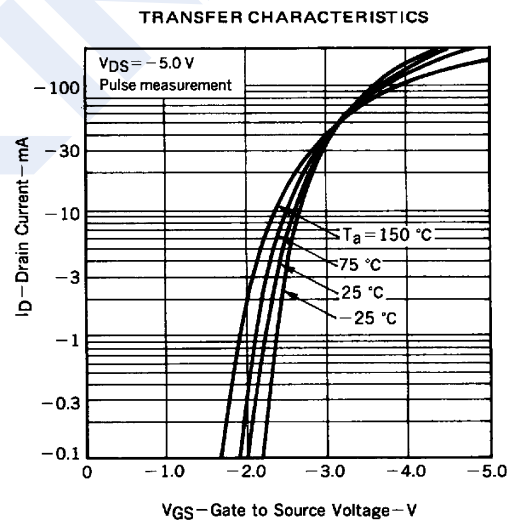
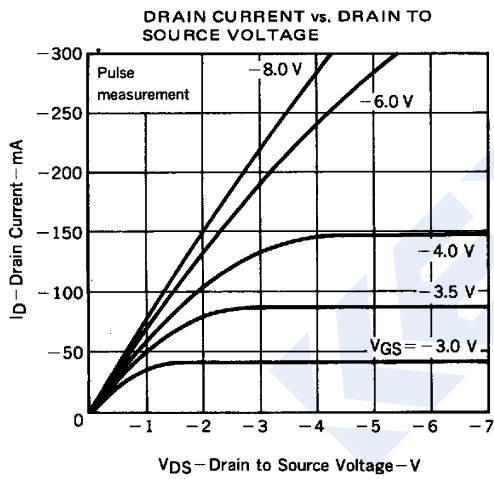
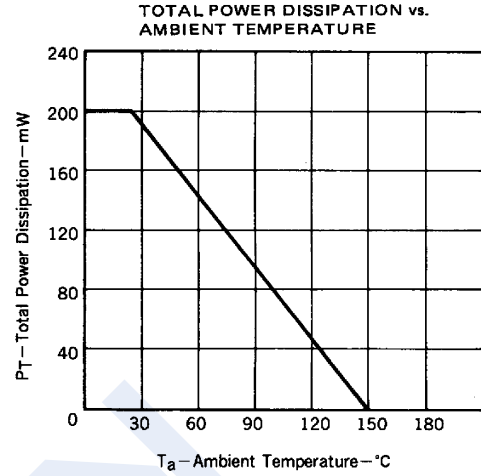
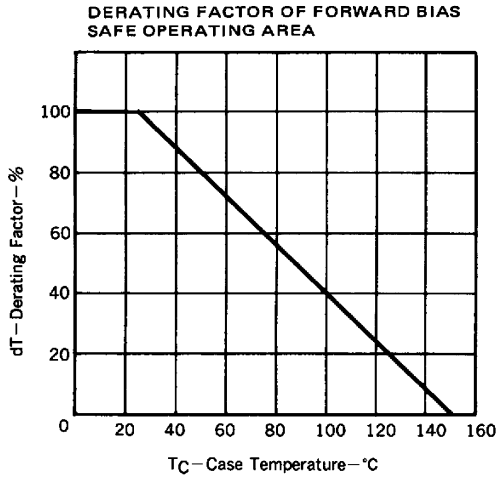
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$V_{DSS}$	$I_D = -250 \mu A, V_{GS} = 0V$	-100			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = -100V, V_{GS} = 0V$			-1	$\mu A$
Gate-Body leakage current	$I_{GSS}$	$V_{DS} = 0V, V_{GS} = \pm 20V$			$\pm 10$	$\mu A$
Gate to Source Cutoff Voltage	$V_{GS(off)}$	$V_{GS} = -5V, I_D = -1mA$	-1.4		-2.4	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS} = -10V, I_D = -10mA$			20	$\Omega$
		$V_{GS} = -4V, I_D = -10mA$			30	
Forward Transconductance	$g_{FS}$	$V_{DS} = -5V, I_D = -10mA$	20	45		mS
Input Capacitance	$C_{iss}$	$V_{GS} = 0V, V_{DS} = -5V, f = 1MHz$		27		pF
Output Capacitance	$C_{oss}$			16		
Reverse Transfer Capacitance	$C_{rss}$			2		
Turn-On Delay Time	$t_{d(on)}$				110	
Turn-On Rise Time	$t_r$	$V_{GS(on)} = -4V, I_D = -10mA,$ $R_L = 500 \Omega, R_G = 10 \Omega, V_{DD} = -5V,$		150		
Turn-Off Delay Time	$t_{d(off)}$			160		
Turn-Off Fall Time	$t_f$			150		

#### ■ Marking

Marking	H18
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## P-Channel MOSFET 2SJ211

■ Typical Characteristics



## P-Channel MOSFET 2SJ211

### Typical Characteristics

